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AMIN, & TUROCY LLP.

FAX NO. 4087493718

16 P. 02 7-15-03

09/891,885

F0279

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application

Applicant(s): Ramsbey, et al.

Art Unit:

2811

Serial No.: 09/891,885

Examiner:

Thomas J. Magee

Filed:

June 26, 2001

Title:

ESD IMPLANT FOLLOWING SPACER DEPOSITION

DECLARATION UNDER 37 C.F.R. §1.131

Mail Stop Non-Fee Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

- I, Mark T. Ramsbey, declare and say as follows:
- I am the inventor of the claims of the above-identified patent application. (1) This Declaration is submitted to establish conception of the invention described and claimed in the above-captioned application in the United States at a date prior to May

09/891,885

F0279

- 29, 2001, which is the date of patent of Fliesler et al. (U.S. Patent 6,238,975 B1) and to establish diligence from at least just prior to May 29, 2001 until constructive reduction to practice, June 26, 2001.
- (2) To establish conception of the invention claimed in the above-identified application prior to May 29, 2001, copies of the relevant portions of an Invention Disclosure describing the invention are enclosed with this Declaration as Exhibit A. Conception and the written description of the invention contained in the Exhibit A were completed prior to May 29, 2001 in this country. Certain information, such as the actual dates and proprietary information, contained on the documents has been removed from the copies.
- (3) Exhibit A, an Invention Disclosure, describes with words and drawings the invention captured by the claims. In particular, the Invention Disclosure indicates facilitating ESD implant following spacer deposition to avoid short channel effect and reduce costs by alleviating extra masking steps. The drawings show the resultant system structure.
- (4) In view of Exhibit A, it can be seen that the invention claimed in the present application was indeed conceived prior to May 29, 2001.
- (5) Before April 12, 2001 and after the date of the Invention Disclosure (before May 29, 2001), discussions concerning the Invention Disclosure with the drafting attorney took place, as needed, for the purpose of ensuring the drafting attorney fully understood the contents of the invention Disclosure.
- (6) On or about April 12, 2001, I received a draft version of a patent application for the instant invention from the drafting attorney.

09/891,885

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- (7) On or about May 11, 2001, a finalized version of the patent application with formals papers was received.
- (8) Executed formal papers and the finalized patent application were returned to the drafting attorney on June 22, 2001.
- I, Mark T. Ramsbey, hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with knowledge that willful false statements and the like are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issued therein.

Mark T. Ramsbey

<u>フ/フ/ゅ3</u> Date

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EXHIBIT A (4 pages)



| AMD INVENTION DISCLOSURE | 7LD 1D# # 0279 Rec'd date |
|---|---|
| | Sunnyvale x42110, return to MS68, Texas x55964 return 4S562 |
| ALL | logy , to which the invention applies (<i>identify</i>): |
| ist 2 to 5 key words useful to search by to find | natents or art related to this invention: |
| =SD, IMPLANT | |
| | |
| Vorking title of invention: ESD Import | AFTER LOOSDACER |
| INVENTOR/SESSION PARTICIPANT ADD | RESS INFORMATION IS ON THE NEXT PAGE (1) |
| oventor's signature: Math Ramster | date: Citizenship: Home telephone:() |
| nventor's printed full name: MARK RAM | パモソ Citizenshin: |
| imployee #: Extension: Mail | stop: Home telephone:() |
| Division: Directorate: Dept #: | Dept : Manager: |
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| ivision: Directorate: Dept #: | Dept: Manager: |
| esidence address: | |
| ost Office address: | |
| ist on additional sheet if there are more co-invento | rs and list total number of inventors here: |
| ame(s) of attorney(s) preferred by inventor(s) to p | tepate patent application, if known: |
| AW FIRM: AMIN, ESCHWEILER & TURO TTORNEYS: Himanshu Amin, Tom Eschweiler, Greg | Y, L.L.P. Turocy, and Don Bortnick |
| Vitness 1 initial: APT 14 & Callistance 2 in | itial: |

| MD INVENTION | DISCLOSURE | TLD I | |
|---|--|----------------------------|--|
| California x42110, return to MS | 58. Texas x55964 return t | o MS562. | Dresden x83401 Silke Kretzschmar at MS E21-PP. |
| | 4 110 40 | | |
| entify known relevant art | (patents, publications, p | moducis): | |
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| | | <u></u> | - CONTRACT FEET TOW |
| tate the problem solved by | this invention: AV | 011) 51-10 | AT CHANNEL EFFECTBY |
| DOING ESD | MPUM AFTER | - <u>LD</u> | ER PROCESS |
| MILINE ST | TEP FUR | CHEMI | Sic [Nicces] |
| inf description and/or sky | etch of invention (nleas | se attach (| copies of AMD patent notebook pages, reports |
| rawings): (FCAT | TACHEP | | |
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| Patent notebook # | Page numbers | | Number of drawings |
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| Witness I initial: | Witness 2 | initial: _ | |
| AMD Inventor Disclosure DB7 | The marks with the same of the | Signal Signal Signal | AMDU GONFIDENTIALS |
| Page 0 | is g Isages (sp.) | a gri | The state of the s |

罗IN PERIPH.

TRADITIONALLY THERE IS AN ADILITIONAL IMPLANT WITH ESD implest THE ELECTRISTATIC DISCHARGE PROTECTION DEVICES. THERE IS A MAJA WHICH PROTECTS THE CTHER DEVICES FROM SHORT CHANNEL PERIONERY EFFECT-

ESO MASK EDD INPAUL 1 LOO MAUK TIED IMPLANT PLUD MAJK PLAD IMPORT

CLOF I. FORM BOLATION (FIELD OX, TRENCH, ETC.)

2. VT IMPUANT SET THRESHOLD VOLTAGE

3. GATE STOF

GA TE POLY DEPOSITION, OPTIONAL WST, POLYCAP, GATEARC

MIKEN Ya- MILL E ETCH GATEL ESD IMPIANT - BO COUP BE A ORP LOD AND

PERPHERY IZEST OF 7 CHIP MAJESO

LOWERS THEET RESITIONER MERELES BIPOLAL

EFFECT WILLIAMS

LOU ED LON TEJO N- TTPE EXAMPLE ESD implant GATE is hearly implant that causes Shortchan, effect Cturns on too easy)

OXIDE, NITHINE, SPACER FORMATION -OXIDE+ RITNUF, ETC.

DEPOSIT SPACER

NOTAKE ETCHRACK

(S/O IMPUNT) IMPLANT PERIPHERY SOURCE DAYN HEHLY AS one solin is GATE lenather Gate. lutities not तंद्यणस्य favored 6000n-

> 8. THERMAL (YUE TO ALTINATE SOME / DARW INPUT)

PROCKEM - SPEED SHORTER CHANNEL DEVICES HAVE Received from < 216 696 8731 > at 7/10/03 7:39:52 AM [Eastern Daylight Time] LANGUEL CONTROL CONTROL FOR THE PROPERTY OF THE P

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EID MICHIT

SCIUTION -

DONST DO ESO MPLANT UNTIL AFTER SPALER ETM

COPE 4 SOME PERIPH Devices

MAJE EJO MPLANT AS GEFORE SO IT ONLY GOES

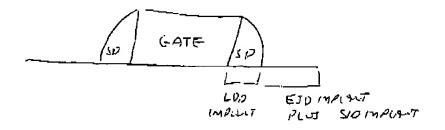
INTO ESO DEVICES

ADVANTAGE DOAN USE HEAVIER DOSE WITHOUT

AS MUCH SHORT CHANNEL EFFECT ON FLOOR VICES.

a narrower gate permitted

FLOW SAME AS REFORE EXCEPT END MASK AND IMPORT NOT IN STEP 5 BUT INSTEP 7



B. NO MASK FOR ESD MPLANT ALL DEVICES GET ESO IMPLANT BUTSWEE IT IS DONE AFTER SPACER IT WILL NOT CAUSE SHORT CHANNEL EFFECT AND WILL NOT - AURT P-CHANNEL DEVICES (P+ SOURCE LONGIN IMPLANT WILL COUNTER PUPE IT) Adu- eliminate mask step